

2N5771

MMBT5771





PNP Switching Transistor

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	15	V
V _{EBO}	Emitter-Base Voltage	4.5	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	М	ах	Units
		2N5771	*MMBT5771	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

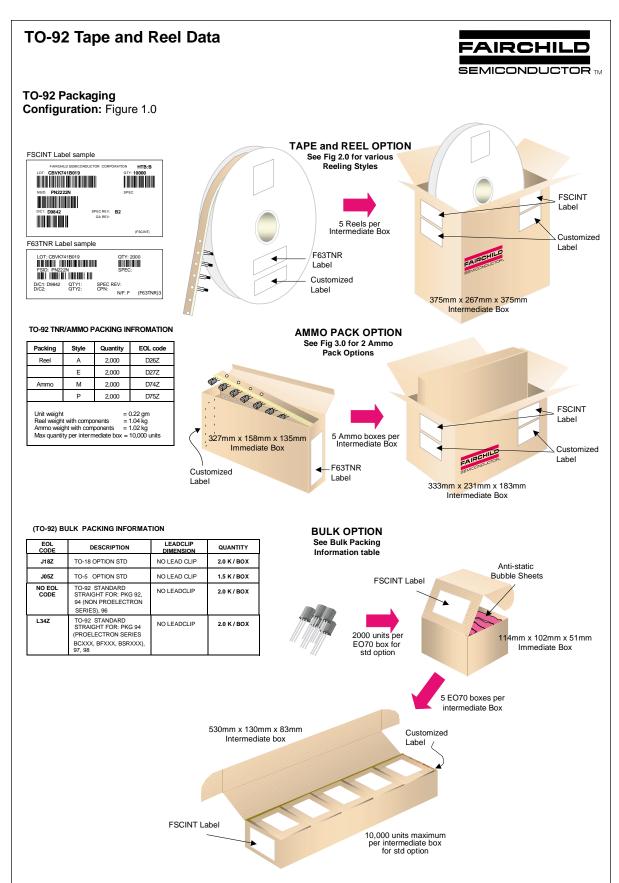
^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP Switching Transistor (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units	
OFF CHAI	RACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	15		V	
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, V_{BE} = 0$	15		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \mu \text{A}, I_{\rm E} = 0$	15		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	4.5		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 8.0 \text{ V}, I_{E} = 0$		10	nA	
I _{CES}	Collector Cutoff Current	V _{CE} = 8.0 V, V _{BE} = 0 V _{CE} = 8.0 V, V _{BE} = 0, T _A = 125°C		10 5.0	nA μA	
I _{EBO}	Emitter Cutoff Current	$V_{CE} = 8.0 \text{ V}, V_{BE} = 0, T_{A} = 125^{\circ}\text{C}$ $V_{EB} = 4.5 \text{ V}, I_{C} = 0$		1.0	μA	
h _{FE}	DC Current Gain	$\begin{split} I_C &= 1.0 \text{ mA}, \ V_{CE} = 0.5 \text{ V} \\ I_C &= 10 \text{ mA}, \ V_{CE} = 0.3 \text{ V} \\ I_C &= 10 \text{mA}, V_{CE} = 0.3 \text{V}, T_A = -55 ^{\circ}\text{C} \end{split}$	35 50 20	120		
		$I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.15 0.18 0.6	V V V	
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.75	0.8 0.95 1.5	V V V	
SMALL SI	GNAL CHARACTERISTICS					
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, I_{E} = 0,$ f = 140 kHz		3.0	pF	
C _{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0,$ f = 140 kHz		3.5	pF	
h _{fe}	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	8.5		MHz	
SWITCHI	NG CHARACTERISTICS					
t _s	Storage Time	$I_C = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$ $I_{B1} = I_{B2} = 1.0 \text{ mA}$		20	ns	
t _{on}	Turn-On Time	$I_C = 10 \text{ mA}, V_{CC} = 1.5 \text{ V},$ $I_B = 1.0 \text{ mA}$				
t _{off}	Turn-Off Time					

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

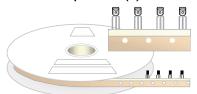


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TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

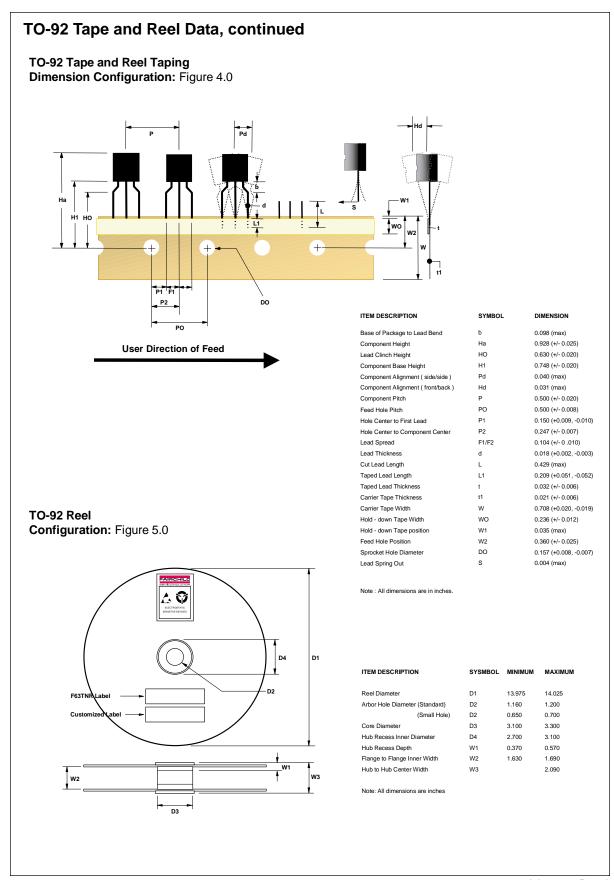
Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0





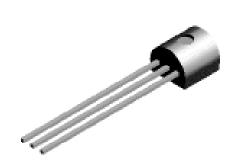
FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

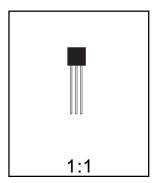


TO-92 Package Dimensions



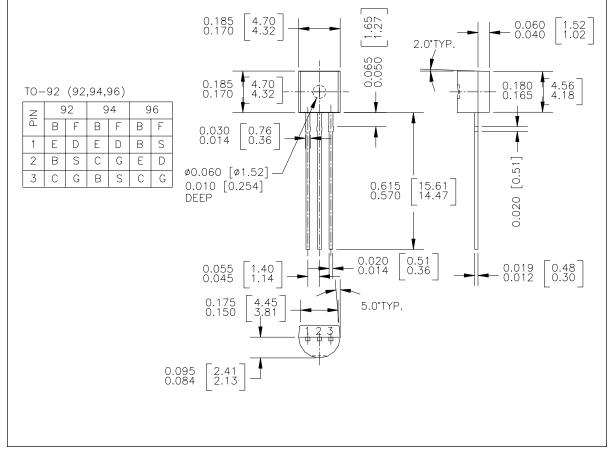
TO-92 (FS PKG Code 92, 94, 96)





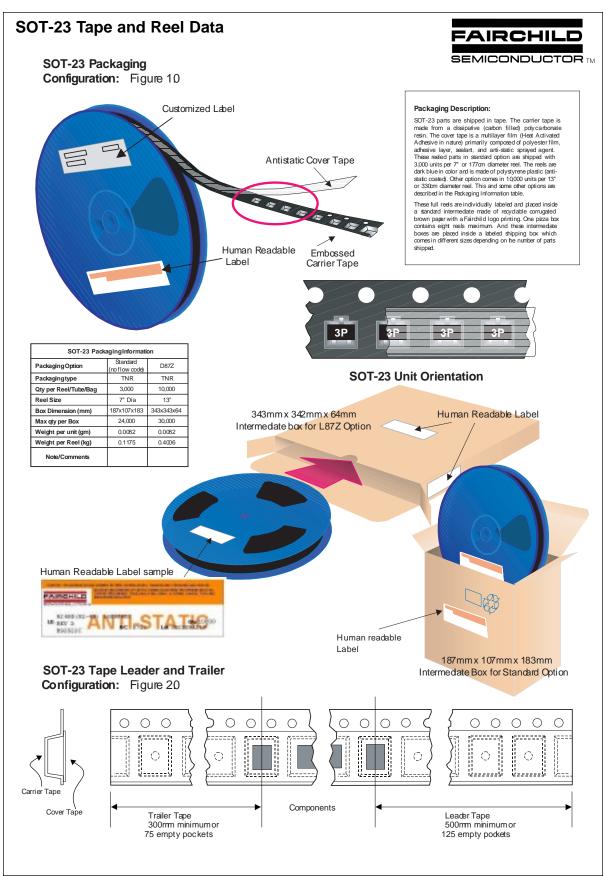
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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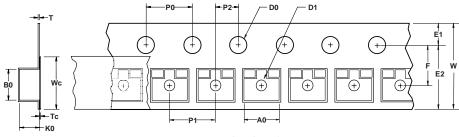
January 2000, Rev. B



SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



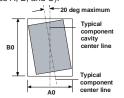
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



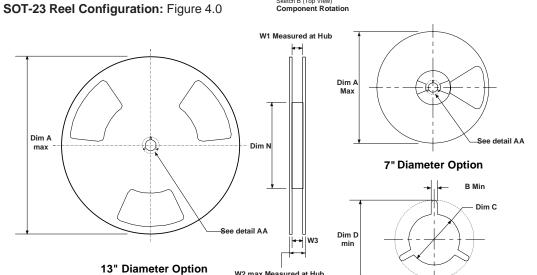
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

DETAIL AA



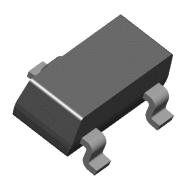
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

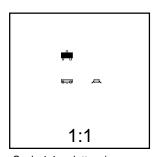
W2 max Measured at Hub

SOT-23 Package Dimensions



SOT-23 (FS PKG Code 49)

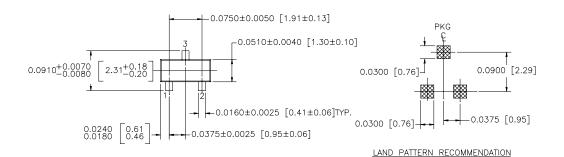


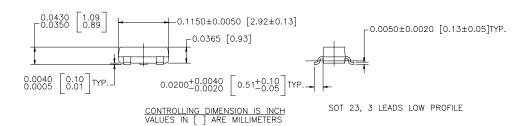


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO -236, VARIATION AB, ISSUE G, DATED JUL 1993

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Rev. G